

# BAS70-00/-04/-05/-06

**PRV : 70 Volts**  
**Io : 200 mA**

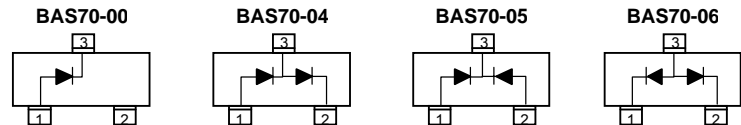
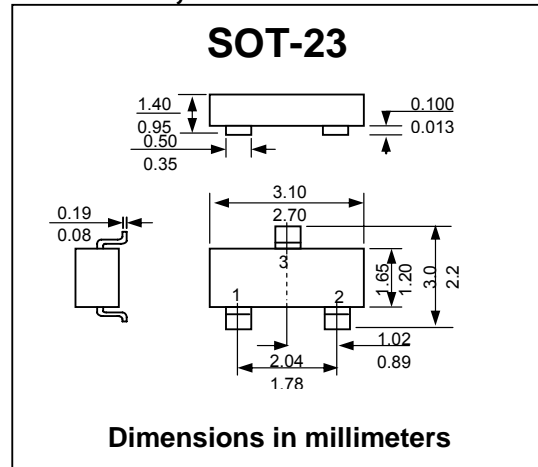
### FEATURES :

- \* These diodes feature very low turn-on voltage
- \* Fast switching
- \* These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- \* **Pb / RoHS Free**

### MECHANICAL DATA :

- \* Case : SOT-23 plastic Case
- \* BAS70-00 Marking Code : 73
- \* BAS70-04 Marking Code : 74
- \* BAS70-05 Marking Code : 75
- \* BAS70-06 Marking Code : 76

## SMALL SIGNAL SCHOTTKY DIODE, SINGLE & DUAL



### MAXIMUM RATINGS AND THERMAL CHARACTERISTICS ( Ta = 25 °C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	70	V
Maximum Working Peak Reverse Voltage	$V_{RWM}$	70	V
Maximum DC Blocking Voltage	$V_R$	70	V
Maximum Forward Continuous Current	$I_F$	200 <sup>(1)</sup>	mA
Maximum Peak Forward Surge Current at $t_p < 1$ s	$I_{FSM}$	600 <sup>(1)</sup>	mA
Total Power Dissipation	$P_{tot}$	200 <sup>(1)</sup>	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	430 <sup>(1)</sup>	K/W
Junction Temperature Range	$T_J$	125	°C
Storage Temperature Range	$T_{STG}$	-65 to +150	°C

### ELECTRICAL CHARACTERISTICS ( Ta = 25 °C, unless otherwise specified.)

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	$I_R = 10 \mu A$ (pulses)	$V_{(BR)}$	70	-	-	V
Leakage Current	$V_R = 50$ V	$I_R$	-	20	100	nA
Forward Voltage (Note 2)	$I_F = 1.0$ mA	$V_F$	-	-	410	mV
	$I_F = 15$ mA	$V_F$	-	-	1	V
Diode Capacitance	$V_R = 0$ V, $f = 1$ MHz	$C_{tot}$	-	1.5	2	pF
Reverse Recovery Time	$I_F = 10$ mA, $I_R = 10$ mA, $I_{rr} = 1$ A, $R_L = 100 \Omega$	$T_{rr}$	-	-	5	ns

#### Notes :

- (1) Device on fiberglass substrate
- (2) Pulse test  $t_p < 300 \mu s$